PCN Number: 202			0240723008.1		PCN	<b>Date:</b> July 23, 2024		July 23, 2024			
Title	Qualification of										Revision, Datasheet
Tierc		update	and add	itiona	tional Assembly Site/BOM options for select devices				devices		
Cus	tomer	Contac	t:	Char	nge l	Management <sup>*</sup>	Team	Dep	Dept:		Quality Services
Proposed 1 <sup>st</sup> Ship Date: October 21, 2024 Sample requests accepted until: August 22, 2					August 22, 2024*						
*Sa	*Sample requests received after August 22, 2024 will not be supported.										
Cha	nge T	уре:									
	Asser	nbly Site			Design				Wa	fer Bump Material	
	Assembly Process					Data Sheet				Wa	fer Bump Process
Assembly Materials					Part number	change	e	$\boxtimes$	Wa	fer Fab Site	
Mechanical Specificatio			on		Test Site				Wa	fer Fab Material	
Packing/Shipping/Labe			eling		Test Process	5		$\boxtimes$	Wa	fer Fab Process	
						DCN Date	sile				

# **PCN Details**

# Description of Change:

Texas Instruments is pleased to announce the qualification of its AIZU fabrication facility as an additional Wafer Fab option in addition to Assembly site/BOM options for the devices listed below.

	Current Fab	Site	Additional Fab Site			
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter	
DFAB	LBCSOI	200 mm	AIZU	LBCSOI2	200 mm	

The die was also changed as a result of the process change.

## Construction differences are as follows:

#### Group 1:

	ASESH	FMX
Wire diam/type	1.3mil Au	0.96mil Cu
Mount compound	EY1000063	4147858
Mold compound	EN2000509	4211880
Package marking	Pin1 stripe, with G4	Pin 1 dot, no G4

#### Group 2:

	Current	Proposed
Wire diam/type	1.3mil Cu	0.96mil Cu

## Group 3:

	TI Clark	TI CDAT
Wire diam/type	1.3mil Cu	0.96mil Cu

# Group 4:

	UTL	TI CDAT
Wire diam/type	1.3mil Cu	0.96mil Cu
Mount compound	PZ0031	4207123
Mold compound	CZ0142	4222198

The datasheets will be changing as a result of the above mentioned changes. The datasheet change details can be reviewed in the datasheet revision history. The links to the revised datasheets are available in the table below.



#### Changes from Revision F (November 2014) to Revision G (July 2024) Updated several specifications to reflect the device characteristics......1 Deleted all references to UCC27210 since device is obsolete......1 Changed Features section: 1) Changed junction temperature range specification from -40°C to 140°C to -40°C to 150°C, 2) Changed peak currents to reflect specification, no change in actual drive strength (from 4A/4A to 3.7A/4.5A. 3) Deleted 0.9-Ω Pullup and Pulldown Resistance since it is not specified in the Electrical Characteristics. 4) Deleted Pseudo-CMOS Compatible Input which is not a feature of the UCC27211A device. 5) Changed typical specifications mentioned for delay matching and propagation delay to reflect the information in the Electrical Characteristics table: from 2-ns delay matching, 18-ns propagation delay to 4-ns Changed Description section: 1) Changed peak current to display typical pull-up/pull-down, no change in actual specification - from 4A4/A to 3.7A/4.5A. 2) Deleted pullup/pulldown resistance information since this is not an actual specification in the Electrical Characteristics table. 3) Changed HS transient tolerance to match the specification in the Absolute Maximum table - from -18V to -(VDD-24)V. 4) Changed delay matching to match specification in the Electrical Characteristics table - from 2ns to 4ns. Updated Absolute Maximum Ratings section to remove "Lead temperature (soldering, 10s)"......5 Updated Recommended Operating Conditions: Operating Junction Temperature maximum changed from Removed specifications with test condition "DDA only" since all specifications apply to all package variants.. 5 Removed specifications for UCC27210. .....5 Updated Supply Currents specifications in the Electrical Characteristics table: 1) I<sub>DD</sub> minimum specification removed. 2) I<sub>DD</sub> typical changed (From: 0.085mA. To: 0.11mA). 3) I<sub>DDO</sub> typical changed (From: 2.5mA. To: 1.4mA). 4) I<sub>DDO</sub> maximum changed (From: 5.2mA. To: 3mA. 5) I<sub>HB</sub> minimum specification removed. 6) I<sub>HBO</sub> typical changed (From: 2.5mA. To: 1.3mA). 7) I<sub>HBO</sub> maximum changed (From: 5mA. To: 3mA). 8) I<sub>HBS</sub> test condition changed to match V<sub>HS</sub> maximum recommended operating conditions (From: 115V. To: 105V). 9) I<sub>HBSO</sub> typical changed (From: 0.07mA. To: 0.03mA). 10) I<sub>HBSO</sub> maximum changed (From: 1.2mA. To: 1mA). .5 Updated Input specifications in the Electrical Characteristics table: UCC27211 V<sub>LIT</sub> minimum changed (From: Updated Bootstrap diode specifications in the Electrical Characteristics table: 1) V<sub>F</sub> maximum changed (From: 0.8V. To: 0.85V). 2) V<sub>FI</sub> typical changed (From: 0.85V. To: 0.9V), and maximum changed (From: 0.95V. To: 1.05V). 3) R<sub>D</sub> test conditions changed (From: 100mA and 80mA. To: 180mA and 160mA). 4) R<sub>D</sub> typical changed (From: $0.5\Omega$ . To: $0.55\Omega$ ). Updated LO/HO Gate Driver specifications in the Electrical Characteristics table: 1) Minimum specification removed for V<sub>LOL</sub>, V<sub>LOH</sub>, V<sub>HOL</sub>, V<sub>HOL</sub>, 2) V<sub>LOL</sub> and V<sub>HOL</sub> typical changed (From 0.09V. To 0.07V). 3) V<sub>LOH</sub> and V<sub>HOH</sub> typical changed (From: 0.16V. To: 0.11V)......5 Updated Switching Characteristics - Propagation Delays table: 1) Changed T<sub>DLFF</sub> and T<sub>DHFF</sub> typicals (From: Updated Switching Characteristics - Delay Matching table: 1) Changed T<sub>MON</sub> and T<sub>MOFF</sub> typicals (From: 2ns. To: 4ns). 2) Changed T<sub>MON</sub> and T<sub>MOFF</sub> across temperature maximum (From: 14ns. To: 17ns)......5 Updated Switching Characteristis - Output Rise and Fall Time table: 1) t<sub>R</sub> typical changed (From: 0.36us. To: Updated Switching Characteristics - Miscellaneous table: t<sub>IN PW</sub> maximum changed (From: 50ns. To: 40ns)..5 Updated all plots in Typical Characteristics section to reflect the typical specification of the device. ......9 Updated Input Stages section to match the input pulldown resistance typical specification in the Electrical Characteristics table, changed from 70kΩ to 68kΩ. Changed input capacitance from 2pF to 4pF. ......13 TEXAS UCC27212 INSTRUMENTS SLUSCO1B - JUNE 2017 - REVISED JULY 2024

C	hanges from Revision A (April 2018) to Revision B (July 2024)
	Changed document title to reflect the device's key features.
	Changed several specifications to reflect the device characteristics
	Changed Features section: 1) Changed sink/source current to use exact typical specification, no change in actual device specification (From: 4-A/4-A To: 3.7-A/4.5-A). 2) Changed T <sub>J</sub> to match improved device specification (From: Specified from -40°C to +140°C. To: Specified from -40°C to +150°C junction temperature range).
	Updated Applications section with list of top 5 typical applications
	Changed Description section: 1) Changed peak currents (From: 4-A source and 4-A sink. To: 3.7A source and 4.5A sink). 2) Changed 5-V turn-off UVLO (From: 5-V UVLO. To: 5-V turn-off UVLO). 3) Changed format for package name from WSON (10) to DPR (WSON, 10). 4) Changed HS pin tolerance to reflect specificatio in Electrical Characteristics table (From: -18V. To: -(24V-VDD)). 5) Updated propagation delay plot
	package
	Updated Recommended Operating Conditions: Operating Junction Temperature maximum changed from 140°C to 150°C
	Updated Thermal Information section to reflect device characteristics.
	Updated Electrical Characteristics and Switching Characteristics tables to remove specifications for 6.8V VDD, leaving the specifications for 12V VDD test condtion, as typically done in gate driver datasheets
	Updated Supply Currents specifications in the Electrical Characteristics table: 1) Minimum specification removed for $I_{DD}$ , $I_{DDO}$ , $I_{HB}$ and $I_{HBO}$ . 2) $I_{DD}$ typical changed (From: 0.085mA. To: 0.11mA). 3) $I_{DDO}$ typical changed (From: 2.5mA. To: 1.4mA). 4) $I_{DDO}$ maximum changed (From: 6.5mA. To: 3mA. 5) $I_{HBO}$ typical changed (From: 2.5mA. To: 1.3mA). 6) $I_{HBO}$ maximum changed (From: 5.1mA. To: 3mA). 8) $I_{HBS}$ test condition changed to match $V_{HS}$ maximum recommended operating conditions (From: 115V. To: 100V). 9) $I_{HBSO}$ typical changed (From: 0.07mA. To: 0.03mA). 10) $I_{HBSO}$ maximum changed (From: 1.2mA. To: 1mA).
	Updated Bootstrap diode specifications in the Electrical Characteristics table: 1) $V_F$ maximum changed (From: 0.8V. To: 0.85V). 2) $V_{FI}$ typical changed (From: 0.85V. To: 0.9V), and maximum changed (From: 0.95V). 3) $R_D$ test conditions changed (From: 100mA and 80mA. To: 180mA and 160mA). 4) $R_D$ typical changed (From: 0.5 $\Omega$ ).
	Updated LO/HO Gate Driver specifications in the Electrical Characteristics table: 1) Minimum specification removed for V <sub>LOL</sub> , V <sub>LOH</sub> , V <sub>HOH</sub> , V <sub>HOH</sub> , 2) V <sub>LOL</sub> and V <sub>HOL</sub> typical changed (From 0.1V. To 0.07V). 3) V <sub>LOH</sub> and V <sub>HOH</sub> typical changed (From: 0.16V. To: 0.11V)
	Updated Propagation Delays specifications in the Switching Characteristics table: 1) Changed $T_{DLFF}$ and $T_{DHFF}$ typicals (From: 16ns. To: 19ns). Updated Output Rise and Fall Time specifications in the Switching Characteristis table: 1) $t_R$ with 1000pF $C_{LOAD}$ changed (From: 7.8ns typical. To: 7.2ns typical). 2) $t_F$ with 1000pF $C_{LOAD}$ changed (From: 6ns typical. To: 5.5ns typical). 3) $t_R$ with 1uF $C_{LOAD}$ changed (From: 0.36us typical. To: 0.27us typical). 4) $t_F$ with 0.1uF $C_{LOAD}$ changed (From: 0.20us typical. To: 0.16us typical)
	Updated all plots in Typical Characteristics section to reflect the typical specification of the device
	Changed typical specifications mentioned in the Overview section to match the device specifications in the Electrical Characteristics table.
	Changed Input Stages section to match the input pulldown resistance typical specification in the electrical
	characteristics table (From: 70kΩ. To: 68kΩ)
	Changed application curves to display propagation delay and rise/fall time plots.



UCC27200, UCC27201 SLUS746D – DECEMBER 2006 – REVISED JULY 2024

_	nanges from Revision C (April 2016) to Revision D (July 2024)  Page 1
	Changed document title to reflect the device's key features. Updated several specifications to reflect the
	device characteristics.
	Updated the numbering format for tables, figures, and cross-references throughout the document
	Changed Features section: 1) Changed junction temperature range specification From: -40°C to 140°C. To:
	-40°C to 150°C. 2) Changed typical propagation delay From: 20ns. To: 22ns. 3) Deleted Greater than 1 MHz
	of Operation since the switching frequency is not a specified parameter. 4) Changed typical bootstrap diode
	resistance From: $0.6\Omega$ . To: $0.65\Omega$ .
	Updated Applications section with list of top 5 typical applications
	Updated Absolute Maximum Ratings section to remove "Power dissipation at TA = 25°C" and "Lead
	temperature (soldering, 10s)". Power dissipation can be calculated with thermal metrics in "Thermal
	Information" table
	Updated Recommended Operating Conditions: Operating Junction Temperature maximum changed from
	140°C to 150°C
	Updated Thermal Information section to reflect device characteristics.
	Updated Supply Currents specifications in the Electrical Characteristics table: 1) I <sub>DD</sub> typical changed (From:
	0.4mA. To: 0.11mA). 2) I <sub>DDO</sub> typical changed (From: 2.5mA for UCC27200 and 3.8mA for UCC27201. To:
	1mA for both). 3) I <sub>DDO</sub> maximum changed (From: 4mA for UC27200 and 5.5mA for UCC27201. To: 3mA for
	both. 4) I <sub>HB</sub> typical changed (From: 0.4mA. To: 0.065mA). 5) I <sub>HBO</sub> typical changed (From: 2.5mA. To: 0.9mA)
	6) I <sub>HBO</sub> maximum changed (From: 4mA. To: 3mA). 7) I <sub>HBS</sub> test condition changed to match V <sub>HS</sub> maximum
	recommended operating conditions (From: 110V. To: 105V). 8) I <sub>HBSO</sub> typical changed (From: 0.1mA.
	To: 0.03mA)
	changed (From: 1.7V typical, 2.5V maximum. To: 1.9V minimum, 2.3V typical, 2.7V maximum). 4) UCC2720 $V_{LIT}$ specifications changed (From: 0.8V minimum, 1.6V typical. To: 1.3V minimum, 1.6V typical, 1.9V maximum). 5) UCC27201 $V_{IHYS}$ typical changed (From: 100mV. To: 700mV). 6) UCC27201 $R_{IN}$ specification changed from (100kΩ minimum, 200kΩ typical, 350kΩ maximum. To: 68kΩ typical)
	Updated Bootstrap diode specifications in the Electrical Characteristics table: 1) R <sub>D</sub> test conditions changed
	(From: 100mA and 80mA. To: 120mA and 100mA). 2) $R_D$ typical changed (From: 0.6 $\Omega$ . To: 0.65 $\Omega$ )
	Updated LO/HO Gate Driver specifications in the Electrical Characteristics table: 1) V <sub>LOL</sub> typical changed
	(From 0.18V. To 0.1V). 2) V <sub>LOH</sub> typical changed (From: 0.25V. To: 0.13V).
	Removed specifications with test conditions "-40°C to 125°C T <sub>J</sub> ", since all parameters are specified from
	-40°C to 150°C T <sub>J</sub> (unless otherwise noted).
	Changed Propagation Delays typical specification (From: 20ns. To: 22ns)
	Updated Output Rise and Fall Time specifications: 1) t <sub>R</sub> typical changed (From: 0.35us. To: 0.26us). 2) t <sub>F</sub>
	typical changed (From: 0.3us. To: 0.22us).
	Updated all plots in Typical Characteristics section to reflect the device's typical specification.
	Updated Input Stages section. 1) Changed UCC27201A input pulldown resistance typical to match the
	specification in the electrical characteristics table (From: 70kΩ. To: 68kΩ). 2) Changed input capacitance
	From: 2pF To: 4pF. 3) Changed UCC27200A input thresholds to 6V and 5.6V to reflect the specification in the
	electrical characteristics table (From: 48% and 45% of VDD. To: 6V and 5.6V)
	Updated Typical Application section to display a different application diagram and detailed design procedure
	since information in legacy datasheet had an outdated circuit with obsolete part numbers
	Changed application curves to display propagation delay and rise/fall time plots.
	Updated Power Supply Recommendations section to fix 3 typos



UCC27200A, UCC27201A SLUSAF9C – FEBRUARY 2011 – REVISED JULY 2024

	ag
Changed document title to reflect key features of the device.	
Updated several specifications to reflect device characteristics.	
Updated Features section: 1) Changed junction temperature range specification from -40°C to 140°C to	
-40°C to 150°C. 2) Changed typical propagation delay from 20ns to 22ns. 3) Deleted Greater than 1MHz	of
Operation since the switching frequency is not a specified parameter. 4) Changed typical bootstrap diode	
resistance from $0.6\Omega$ to $0.65\Omega$	
Updated Applications section with list of top 5 typical applications	
Deleted any reference to UCC27200A in DRC package in this data sheet since this package variant is obsolete.	
Updated Pin Configuration and Functions section pin diagrams and pin description to indicate that the	
PowerPAD is internally connected to the VSS pin on the DRC package only.	
Updated Absolute Maximum Ratings section to remove "Power dissipation at TA = 25°C" and "Lead	
temperature (soldering, 10s)". Power dissipation can be calculated with thermal metrics in "Thermal	
Information" table.	
Updated Recommended Operating Conditions: Operating Junction Temperature maximum changed from	
140°C to 150°C	
Updated Thermal Information section to reflect device characteristics.	
Updated Supply Currents specifications in the Electrical Characteristics table: 1) I <sub>DD</sub> typical changed (Fro	
0.4mA. To: 0.11mA). 2) I <sub>DDO</sub> typical changed (From: 2.5mA for UCC27200 and 3.8mA for UCC27201. To:	
1mA for both). 3) I <sub>DDO</sub> maximum changed (From: 4mA for UC27200 and 5.5mA for UCC27201. To: 3mA for UCC27201.	
both. 4) I <sub>HB</sub> typical changed (From: 0.4mA. To: 0.065mA). 5) I <sub>HBO</sub> typical changed (From: 2.5mA. To: 0.9n	
6) I <sub>HBO</sub> maximum changed (From: 4mA. To: 3mA). 7) I <sub>HBS</sub> test condition changed to match V <sub>HS</sub> maximum	
recommended energting conditions (From: 110)/ To: 105\(\)\ 0\(\)\ typical changed (From: 0.1m)	
recommended operating conditions (From: 110V. To: 105V). 8) I <sub>HBSO</sub> typical changed (From: 0.1mA.	
To: 0.03mA)	
To: 0.03mA)  Updated Input specifications in the Electrical Characteristics table: 1) UCC27200 V <sub>HIT</sub> typical changed (Fom: 5.8V. To: 6V). 2) UCC27200 V <sub>LIT</sub> typical changed (From: 5.4V. To: 5.6V). 3) UCC27201 V <sub>HIT</sub> specifications changed (From: 1.7V typical, 2.5V maximum. To: 1.9V minimum, 2.3V typical, 2.7V maximum). 4) UCC27 V <sub>LIT</sub> specifications changed (From: 0.8V minimum, 1.6V typical. To: 1.3V minimum, 1.6V typical, 1.9V maximum). 5) UCC27201 V <sub>IHYS</sub> typical changed (From: 100mV. To: 700mV). 6) UCC27201 R <sub>IN</sub> specifications	on 20 ion
To: $0.03\text{mA}$ )	20 ion
To: $0.03\text{mA}$ )	20 ion ed
To: $0.03\text{mA}$ )	20 ion ed
To: $0.03\text{mA}$ )	rom 220 ion ed
To: $0.03\text{mA}$ )	roms 220 ion ed
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To: 0.03mA)	roms 220 ion: ed
To: 0.03mA)	roms 220 ion: ed
To: 0.03mA)	ion ion ed 
To: 0.03mA)	roms r200 ions ed



UCC27211A SLUSBL4D – AUGUST 2013 – REVISED JULY 2024

hanges from Revision C (October 2015) to Revision D (July 2024)  Pag
Changed document title to reflect the device's key features.
Changed several specifications to reflect the device characteristics
Removed 8-pin SOIC and 10-pin SON packages from the data sheet
Changed Features section: 1) Changed junction temperature range specification (From: -40°C to 140°C. To: -40°C to 150°C). 2) Deleted HBM and CDM classification levels, no change in ratings in the ESD table. 3) Changed peak currents to reflect specification, no change in actual drive strength (From: 4A/4A. To: 3.7A/4.5A). 4) Deleted 0.9-Ω Pullup and Pulldown Resistance since it is not specified in the Electrical Characteristics. 5) Deleted Pseudo-CMOS Compatible Input which is not a feature of UCC27211A device
Updated Applications section with list of top 5 typical applications
Changed in Description section: 1) Added new D (SOIC, 8) package variant. 2) Changed peak current to display typical pull-up/pull-down, no chang in actual specification (From: 4A4/A. To: 3.7A/4.5A). 3) Deleted pullup/pulldown resistance information since this is not an actual specification in the electrical charactersitics table. 4) Updated propagation delay plot with new data. 5) Changed HS transient tolerance to match the specification in the Absolute Maximum table (From: -18V. To: -(24-VDD)V.
Changed the VSON pinout view from top to bottom
Updated Recommended Operating Conditions: Operating Junction Temperature maximum changed from 140°C to 150°C
Updated Thermal Information section to reflect device characteristics.
Updated Supply Currents specifications in the Electrical Characteristics table: 1) Minimum specification removed for $I_{DD}$ , $I_{DDO}$ , $I_{HB}$ and $I_{HBO}$ . 2) $I_{DD}$ typical changed (From: 0.085mA. To: 0.11mA). 3) $I_{DDO}$ typical changed (From: 2.6mA. To: 1.4mA). 4) $I_{DDO}$ maximum changed (From: 6.5mA. To: 3mA. 5) $I_{HBO}$ typical changed (From: 2.5mA. To: 1.3mA). 6) $I_{HBO}$ maximum changed (From: 5.1mA. To: 3mA). 8) $I_{HBS}$ test condition changed to match $V_{HS}$ maximum recommended operating conditions (From: 115V. To: 105V). 9) $I_{HBSO}$ typical changed (From: 0.07mA. To: 0.03mA). 10) $I_{HBSO}$ maximum changed (From: 1.2mA. To: 1mA).
Updated Input specifications in the Electrical Characteristics table: 1) V <sub>HIT</sub> minimum changed (From: 1.9V. To 1.7V). 2) V <sub>LIT</sub> minimum changed (From: 1.3V. To: 1.2V)
changed (From: 0.5Ω. To: 0.55Ω)
Updated LO/HO Gate Driver specifications in the Electrical Characteristics table: 1) Minimum specification removed for V <sub>LOL</sub> , V <sub>LOH</sub> , V <sub>HOL</sub> , V <sub>HOH</sub> . 2) V <sub>LOL</sub> and V <sub>HOL</sub> typical changed (From 0.1V. To 0.07V). 3) V <sub>LOH</sub> and V <sub>HOH</sub> typical changed (From: 0.16V. To: 0.11V)
Updated Switching Characteristics - Propagation Delays table: 1) Changed T <sub>DLFF</sub> and T <sub>DHFF</sub> typicals (From:
16ns. To: 19ns).
Updated Switching Characteristis - Output Rise and Fall Time table: 1) t <sub>R</sub> typical changed (From: 0.36us. To 0.27us). 2) t <sub>F</sub> typical changed (From: 0.15us. To: 0.16us).
Updated Switching Characteristics - Miscellaneous table: t <sub>IN PW</sub> maximum changed (From: 50ns. To: 40ns).
Obdated Switchilly Characteristics - Miscellaneous table, the big maximum changed reform some no. 400st.
Updated all plots in Typical Characteristics section to reflect the typical specification of the device
Updated all plots in Typical Characteristics section to reflect the typical specification of the device
Updated all plots in Typical Characteristics section to reflect the typical specification of the device

Product Folder	Current Datasheet Number	New Datasheet Number	Link to full datasheet
UCC27211	SLUSAT7F	<b>SLUSAT7G</b>	http://www.ti.com/product/UCC27211
UCC27212	SLUSCO1A	SLUSCO1B	http://www.ti.com/product/UCC27212
UCC2720x	SLUS746C	SLUS746D	http://www.ti.com/product/UCC27200
UCC2720xA	SLUSAF9B	SLUSAF9C	http://www.ti.com/product/UCC27200A
UCC27211A	SLUSBL4C	SLUSBL4D	http://www.ti.com/product/UCC27211A

Qual details are provided in the Qual Data Section.

# **Reason for Change:**

These changes are part of our multiyear plan to transition products from our 150-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

## **Impact on Environmental Ratings:**

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	<b>Green Status</b>	IEC 62474
No Change	No Change	No Change	No Change

# **Changes to product identification resulting from this PCN:**

# Fab Site

# **Information:**

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City	
DL-LIN	DLN	USA	Dallas	
AIZU	CU2	JPN	Aizuwakamatsu-shi	

#### Die Rev:

Current New

Die Rev [2P]	Die Rev [2P]
A, C, D	A

**Assembly Site Information:** 

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City	
UTL	NSE	THA	Bangkok	
TI CLARK	QAB	PHL	Angeles City, Pampanga	
ASESH	ASH	CHN	Shanghai	
TI Mexico	MEX	MEX	Aguascalientes	
CDAT	CDA	CHN	Chengdu	

Sample product shipping label (not actual product label):

TEXAS
INSTRUMENTS
MADE IN: Malaysia
2DC: 2Q:

MSL 2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04

OPT: ITEM:

5A (L)T0:1750



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483812

(2P) REV: (V) 0033347 (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MYS

# **Product Affected:**

# **Group 1 Device List:**

UCC27200ADDAR	UCC27201ADDAR	UCC27201DDAR	UCC27211DDAR
UCC27200DDAR			

## **Group 2 Device List:**

UCC27200ADR	UCC27201ADR	UCC27201DR	UCC27211DR
UCC27200DR			

## **Group 3 Device List:**

UCC27201ADRCR UCC27201ADPRR UCC27211DPRR UCC27212DPF
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# **Group 4 Device List:**

UCC27200ADRMR	UCC27201ADRMR	UCC27211ADRMR
UCC27200DRMR	UCC27201DRMR	UCC27211DRMR

For alternate parts with similar or improved performance, please visit the product page on <a href="II.com">II.com</a>

#### **Qualification Results**

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Name	Condition	Duration	Qual Device: UCC27301ADR	QBS Reference: UCC27301AQDDARQ1	QBS Reference: TCAN1043ADRQ1
HAST	A3	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0
UHAST	A3	Autoclave	121C/15psig	96 Hours	-	3/231/0	-
UHAST	A3	Unbiased HAST	130C/85%RH	96 Hours	-	-	3/231/0
TC	A4	Temp Cycle	-65C/150C	500 Cycles	-	3/231/0	3/231/0
HTSL	A4	High Temp Storage	150C	1000 Hours	-	3/135/0	3/135/0
HTOL	B1	Life Test	125C	1000 Hours	-	-	1/77/0

Туре	#	Test Name	Condition	Duration	Qual Device: UCC27301ADR	QBS Reference: UCC27301AQDDARQ1	QBS Reference: TCAN1043ADRQ1
HTOL	B1	Life Test	150C	300 Hours	-	3/231/0	-
ELFR	B2	Early Life Failure Rate	150C	24 Hours	-	3/2400/0	-
SD	C3	PB-Free Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes)	-	-	1/15/0	-
PD	C4	Physical Dimensions	Cpk>1.67	-	-	3/30/0	3/30/0
ESD	E2	ESD CDM	-	500 Volts	-	1/3/0	1/3/0
ESD	E2	ESD HBM	-	2000 Volts	-	1/3/0	1/3/0
LU	E4	Latch-Up	Per JESD78	-	-	1/6/0	1/6/0
CHAR	E5	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	-	3/90/0	3/90/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2403-170

#### **Qualification Results**

#### Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Name	Condition	Duration	Qual Device: UCC27301AQDRCRQ1	Qual Device: UCC27311AQDRCRQ1	QBS Reference: TLC69601QRTWRQ1	QBS Reference: UCC27301AQDDARQ1	QBS Reference: LP8868ZQDMTRQ1	QBS Reference: LM5149QRGYRQ1	QBS Reference: LM5149RGYR
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	-	3/231/0	3/231/0	1/77/0	1/77/0	3/231/0
UHAST	АЗ	Autoclave	121C/15psig	96 Hours	1/77/0	-	-	3/231/0	-	-	-
UHAST	АЗ	Unbiased HAST	130C/85%RH	96 Hours	-	-	3/231/0	-	1/77/0	-	3/231/0
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	-	3/231/0	3/231/0	1/77/0	1/77/0	3/231/0
HTSL	A6	High Temperature Storage Life	150C	1000 Hours	-	-	3/135/0	3/135/0	1/45/0	-	3/135/0
HTOL	B1	Life Test	125C	1000 Hours	-	-	1/77/0	-	1/77/0	-	-
HTOL	B1	Life Test	150C	300 Hours	-	-	-	3/231/0	-	1/77/0	3/231/0
ELFR	B2	Early Life Failure Rate	150C	24 Hours	-	-	-	3/2400/0	-	-	-
SD	C3	PB-Free Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes)	-	-	-	-	1/15/0	-	-	-
PD	C4	Physical Dimensions	Cpk>1.67	-	1/10/0	-	3/30/0	3/30/0	1/10/0	-	3/30/0
ESD	E2	ESD CDM	-	500 Volts	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0

Туре	#	Test Name	Condition	Duration	Qual Device: UCC27301AQDRCRQ1	Qual Device: UCC27311AQDRCRQ1	QBS Reference: TLC69601QRTWRQ1	QBS Reference: UCC27301AQDDARQ1	QBS Reference: LP8868ZQDMTRQ1	QBS Reference: LM5149QRGYRQ1	QBS Reference: LM5149RGYR
ESD	E2	ESD HBM	-	2000 Volts	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0
LU	E4	Latch-Up	Per JESD78	-	1/6/0	1/6/0	1/6/0	1/6/0	1/6/0	1/6/0	1/6/0
CHAR	E5	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	-	3/90/0	3/90/0	1/30/0	3/90/0	3/90/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
  The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 F
   The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2303-050

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

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